

1

" " " "

2021

()

" ...

1-100

t

t

t

t

t

u

t

t

t

t

u

2021

t

t

3

28

u

1

t

2

u

u

u

5

u

4

6

u

4

35

0.1nmU

1.3

u

t

-

u

u

10-1773

K

t

u

1.4

1~30 THzt

10

t

30

t

t

10

t 1~30 THzt t u
1.5 t

t u

u 2-3 t

200 °C

k u

3 nm 125 cm²/ V·s

12 nm 0.7 V

1 mA/ m 10⁸u 1.5 GHz

u u

2.2

3

/

N/PMOS 10 nm

200 mV N/P

1×10⁻⁹ ·cm² 0.7 V

400 A/ m 70 mV/dec

10⁷

16K SRAM

30% u

2.3

t N/P t

MOS t

u 8 t 99.9%

MOS N/P

50 cm²/ V·s t
t

10⁵

SPICE

u

2.4 5

10

t

t

u 12

5

cmHz^{1/2}W⁻¹

400-1550 nm

128™ 128

u

2.6

t

4

>300 cm²/ V·s

>70%

<1 nmt

<2 Vt

<0.5 kA/cm²

3

u

2.7

u

6

0.5 nm

95%

95%

15000 cm²/ V·s

30 Gbit/su

3.

3.1

t

u

3.2

t

t

t

3-5

pM

1

u

3.3

t

t

u

u

1-2

t

1-2

1-2

1-2

u

3.4

t t

t

u 3-4

u 1

u

3.5 t t

- t

t t u

0~70%

50 MPa 200 MPa 10~200%

100

-

20-100 μm 200 kPa 2 GPa

>5 MPa u 2-3 u

3.6

t

t t t

u 2-3

3.7

4
3 t 1
1
2 u
u
2-3
>10⁵
675-2000 cm⁻¹
2-3
C-Ot CH-O 2-3
2-3

u

3.8

t t / /
u
10 30% 400-700 nm 100
mm² 1 / u

3.9

t u

50 W/m³

3.10 - u

t -

-

-

u

/

-

50 /

u

4.

4.1

t

t

t

t

t

t

t

t

u

4.2

u

-

-

u

t

u

4.3

t

t

u

t

t

t

u

4.4

/

5

4

2

u

4.5

u

u